

APR 1 2003  
U.S. PATENT AND TRADEMARK OFFICE

15.55/6364/

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of ) Examiner: T. L. Dickey  
EBINA )  
Serial No.: 10/050,793 ) Art Unit: 2826  
Filing Date: January 18, 2002 )  
For: SEMICONDUCTOR DEVICES )  
AND METHODS FOR )  
MANUFACTURING THE SAME ) **AMENDMENT**

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sirs:

In response to the Office Action dated December 4, 2002 in the above-referenced application, response to which is due April 4, 2003 with a one-month extension of time (petition for which is attached hereto), please enter and consider the following amendments and remarks:

IN THE FIGURES:

Applicant proposes to amend Fig. 2 as shown in red on the attached sheet.

IN THE CLAIMS:

Please cancel claims 16-22 without prejudice.

Please amend claims 1-2, 4, 6-7 and 9-14 as follows:

1. (Amended) A semiconductor device comprising:  
an insulation layer;  
a semiconductor layer formed on the insulation layer;  
an element isolation region formed in the semiconductor layer; and  
a first element forming region and a second element forming region defined by the element isolation region;

wherein the first element forming region includes both a first bi-polar transistor and a first field effect transistor;

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